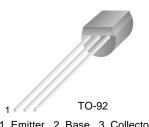


KSP5179

High Frequency Transistor



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

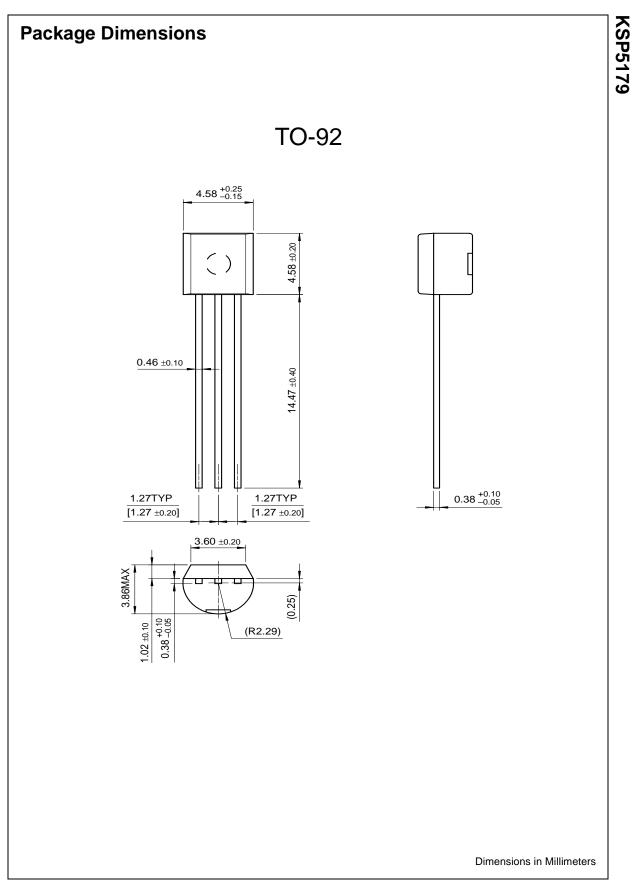
Absolute Maximum Ratings $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	2.5	V
I _C	Collector Current	50	mA
P _C	Collector Power Dissipation (T _a =25°C)	200	mW
	Derate above 25°C	1.6	mW/°C
P _C Collector Power Dissipation (T _C =25°C) Derate above 25°C	Collector Power Dissipation (T _C =25°C)	300	mW
	Derate above 25°C	2.4	mW/°C
Тј	Junction Temperature	150	°C
Т _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V_{CEO} (sus)	Collector-Emitter Sustaining Voltage	I _C =3mA, I _B =0	12		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =10μA, I _E =0	20		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	2.5		V
I _{CBO}	Collector Cut-off Current	V _{CB} =15V, I _E =0 V _{CB} =15V, I _E =0, Ta=150°C		0.02 1	μΑ μΑ
h _{FE}	DC Current Gain	V _{CB} =1V, I _C =3mA	25	250	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		0.4	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		1	V
f _T	Current Gain Bandwidth Product	V _{CE} =6V, I _C =5mA	900	2000	MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=0.1 to1 MHz		1	pF
h _{fe}	Small Signal Current Gain	V _{CE} =6V, I _C =2mA, f=1KHz	25	300	
$C_{c \cdot rbb'}$	Collector Base Time Constant	V _{CE} =6V, I _E =2mA, f=31.9MHz	3	14	ps
NF	Noise Figure	V_{CE} =6V, I _C =1.5mA, f=200MHz R _S =50 Ω		4.5	dB

KSP5179



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